1.3MHz, 70µA, CMOS RRIO Operational Amplifiers

General Description

The LTC8541 (single), LTC8542 (dual) and LTC8544 (quad) are low voltage micro power CMOS voltage feedback operational amplifiers. With an excellent bandwidth of 1.3 MHz, a slew rate of 1.1 V/μs, and a quiescent current of 70 μA per amplifier at 5V, the LTC854x family can be designed into a wide range of applications.

The LTC854x op-amps are specifically designed for general-purpose applications with optimal performance. They have a wide input common-mode voltage range and excellent output voltage swings, and the maximum input offset voltage are ± 2.5 mV. These parts provide rail-to-rail output swing into heavy loads. The LTC854x family is specified for single or dual power supplies of +2.0 V to +5.5 V. All models are specified over the extended industrial temperature range of -40 $^{\circ}$ C to +125 $^{\circ}$ C.

The LTC8541 is available in 5-lead SC70 and SOT-23, and 8-lead SOIC packages. The LTC8542 is available in 8-lead DFN, MSOP and SOIC packages. The LTC8544 is available in 14-lead TSSOP and SOIC packages.

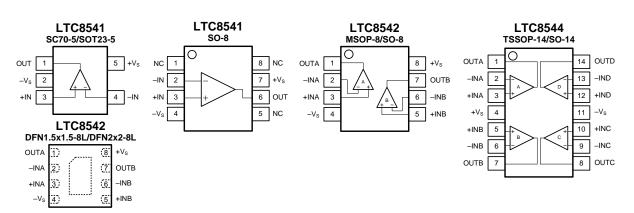
Features and Benefits

- High Gains of >102 dB for Active Filters and Gain Stages
- Low Offset Voltage: ±2.5 mV Maximum with 2 µV/°C Low Drift
- Gain-Bandwidth Product: 1.3 MHz
- High Slew Rate: 1.1 V/µs
- Low Power: 70 μA per Amplifier Supply Current
- Settling Time to 0.1% with 2V Step: 1.5 μs
- Unity Gain Stable
- Rail-to-Rail Input and Output
 - Input Voltage Range: -0.1 to +5.1 V at 5V Supply
- Operating Power Supply: +2.0 to +5.5 V
- Operating Temperature Range: -40 °C to +125 °C
- ESD Rating: HBM 4kV, CDM 2kV

Applications

- Smoke/Gas/Environment Sensors
- Audio Outputs
- Active Filters
- ASIC Input or Output Amplifier
- Sensor Interfaces
- Portable Equipment
- Battery-Powered Instrumentation

Pin Configurations (Top View)







Pin Description

Symbol	Description
–IN	Inverting input of the amplifier. The voltage range can go from (V _{S-} $-$ 0.1V) to (V _{S+} + 0.1V).
+IN	Non-inverting input of the amplifier. This pin has the same voltage range as -IN.
+V _S	Positive power supply. The voltage is from 2.0V to 5.5V. Split supplies are possible as long as the voltage between V_{S+} and V_{S-} is between 2.0V and 5.5V. A bypass capacitor of 0.1µF as close to the part as possible should be used between power supply pins or between supply pins and ground.
-V _s	Negative power supply. It is normally tied to ground. It can also be tied to a voltage other than ground as long as the voltage between V_{S+} and V_{S-} is from 2.0V to 5.5V. If it is not connected to ground, bypass it with a capacitor of 0.1µF as close to the part as possible.
OUT	Amplifier output.
N/C	No internal connection.

Ordering Information

Type Number	Package Name	Package Quantity	Marking Code
LTC8541XC5/R6	SC70-5	Tape and Reel, 3 000	AG1
LTC8541XT5/R6	SOT23-5	Tape and Reel, 3 000	AG1
LTC8541XS8/R8	SO-8	Tape and Reel, 4 000	AG1X
LTC8542XF8S/R10	DFN1.5x1.5-8L	Tape and Reel, 5 000	C42
LTC8542XF8/R6	DFN2x2-8L	Tape and Reel, 3 000	C42
LTC8542XV8/R6	MSOP-8	Tape and Reel, 3 000	AG2X
LTC8542XS8/R8	SO-8	Tape and Reel, 4 000	C42I X
LTC8544XT14/R6	TSSOP-14	Tape and Reel, 3 000	AG4 X
LTC8544XS14/R5	SO-14	Tape and Reel, 2 500	C44I X

Limiting Value

In accordance with the Absolute Maximum Rating System (IEC 60134).

Parameter	Absolute Maximum Rating			
Supply Voltage, V_{S+} to V_{S-}	10.0V			
Common-Mode Input Voltage	$V_{S-} - 0.3V$ to $V_{S+} + 0.3V$			
Storage Temperature Range	–65℃ to +150℃			
Junction Temperature	160°ℂ			
Lead Temperature Range (Soldering 10 sec)	260 ℃			
	HBM ±4 000V			
Electrostatic Discharge Voltage	CDM ±2 000V			
	MM ±400V			





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Electrical Characteristics

 $V_S=5.0V,~T_A=+25\, {\rm C},~V_{CM}=V_S/2,~V_O=V_S/2,~and~R_L=10k\Omega~connected~to~V_S/2,~unless~otherwise~noted.$ Boldface limits apply over the specified temperature range, $T_A=-40~to~+125~{\rm C}.$

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit	
INPUT CH	HARACTERISTICS						
V _{os}	Input offset voltage		-2.5	±0.5	+2.5	mV	
V _{os} TC	Offset voltage drift	over Temperature		2		μV/°C	
				1			
I _B	Input bias current	T _A = +85 °C		150		pΑ	
		T _A = +125 ℃		500			
I _{os}	Input offset current			1		pА	
V_{CM}	Common-mode voltage range		V _{S-} -0.1		V _{S+} +0.1	V	
		V _{CM} = 0.05V to 3.5V	80	97			
CMDD	Common-mode rejection	over Temperature	70			- 40	
CMRR	ratio	$V_{CM} = V_{S-} - 0.1 \text{ to } V_{S+} + 0.1 \text{ V}$	70	82		- dB	
		over Temperature	66			_	
		$R_L = 10k\Omega$, $V_O = 0.05$ to 3.5 V	102	116			
۸	Onen leen veltere rein	over Temperature	90			– dB	
A_{VOL}	Open-loop voltage gain	$R_L = 2k\Omega$, $V_O = 0.15$ to 3.5 V	93	108			
		over Temperature	82				
R _{IN}	Input resistance		100			GΩ	
<u> </u>	Innut conscitones	Differential		2.0		pF	
C _{IN}	Input capacitance	Common mode		3.5			
OUTPUT	CHARACTERISTICS						
V	Lligh output voltage quing	$R_L = 50 \text{ k}\Omega$		V _{S+} -3		— mV	
V _{OH}	High output voltage swing	$R_L = 2 k\Omega$		V _{S+} -65			
\	Law output valtage owing	$R_L = 50 \text{ k}\Omega$		V _S _+2		– mV	
V _{OL}	Low output voltage swing	$R_L = 2 k\Omega$		V _{S-} +45			
7	Closed-loop output impedance	f = 200kHz, G = +1		0.4		0	
Z _{OUT}	Open-loop output impedance	$f = 1MHz$, $I_0 = 0$		2.6		— Ω	
ı	Short-circuit current	Source current through 10Ω		45 50		mA	
I _{SC}	Short-circuit current	Sink current through 10Ω					
DYNAMIC	PERFORMANCE						
GBW	Gain bandwidth product	f = 1kHz		1.3		MHz	
Фм	Phase margin	C _L = 100pF		66		٥	
SR	Slew rate	$G = +1, C_L = 100pF, V_O = 1.5V \text{ to } 3.5V$		1.1		V/µs	
	Cattling time	To 0.1%, G = +1, 2V step		1.5		- µs	
t _S	Settling time	To 0.01%, G = +1, 2V step		1.8			
THD+N Total harmonic distortion + noise		$f = 1kHz, G = +1, V_O = 3V_{PP}$	0.002		%		





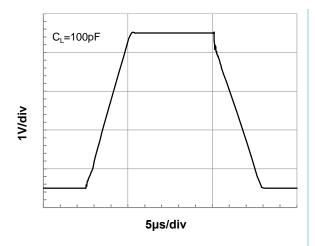
Electrical Characteristics (continued)

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit				
NOISE PERFORMANCE										
V _n	Input voltage noise	f = 0.1 to 10 Hz		6		μV_{P-P}				
e _n	Input voltage noise density	f = 1kHz		27		nV/√Hz				
I _n	Input current noise density	f = 1kHz		4		fA/√Hz				
POWERS	SUPPLY									
V _S	Operating supply voltage		2.0		5.5	V				
PSRR	Power supply rejection	$V_{\rm S}$ = 2.0V to 5.5V, $V_{\rm CM}$ < $V_{\rm S+}$ - 2V	82	102		٩D				
FORK	ratio	over Temperature	75			– dB				
	Quiescent current (per			70	120					
l _Q	amplifier)	over Temperature			150	– μA				
THERMA	L CHARACTERISTICS									
T _A	Operating temperature range		-40		+125	$^{\circ}\! \mathbb{C}$				
		SC70-5		333						
	Package Thermal Resistance	SOT23-5		190						
		DFN2x2-8L								
θ_{JA}		MSOP-8		216		°C/W				
		SO-8		125		_				
		TSSOP-14 112				_				
		SO-14		115		_				

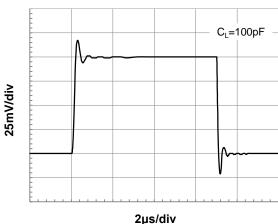
1.3MHz, 70µA, CMOS RRIO Operational Amplifiers

Typical Performance Characteristics

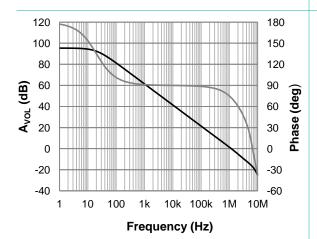
At T_A = +25 °C, V_{CM} = $V_S/2$, and R_L = 10k Ω connected to $V_S/2$, unless otherwise noted.



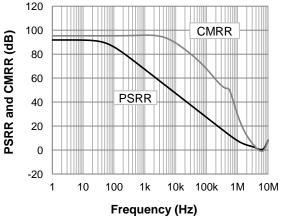
Large Signal Step Response.



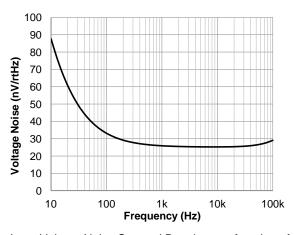
Small Signal Step Response.



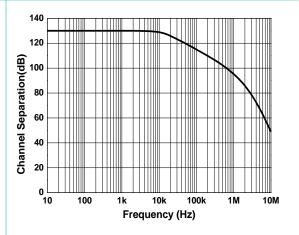
Open-loop Gain and Phase as a function of Frequency.



Power Supply and Common-mode Rejection Ratio as a function of Frequency.



Input Voltage Noise Spectral Density as a function of Frequency.



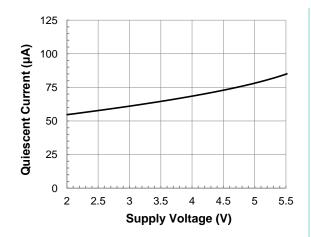
Channel Separation as a function of Frequency.



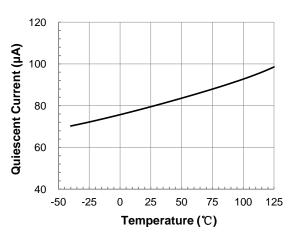


Typical Performance Characteristics (continued)

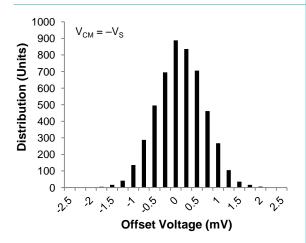
At $T_A = +25\, \text{C}$, $V_{CM} = V_S/2$, and $R_L = 10 \text{k}\Omega$ connected to $V_S/2$, unless otherwise noted.



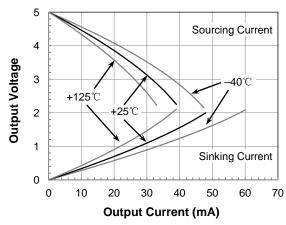
Quiescent Current as a function of Supply Voltage.



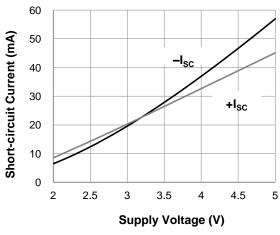
Quiescent Current as a function of Temperature.



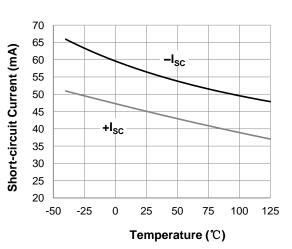
Input Offset Voltage Production Distribution.



Output Voltage Swing as a function of Output Current.



Short-circuit Current as a function of Supply Voltage.



Short-circuit Current as a function of Temperature.



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Application Notes

LOW INPUT BIAS CURRENT

The LTC854x family is a CMOS op-amp family and features very low input bias current in pA range. The low input bias current allows the amplifiers to be used in applications with high resistance sources. Care must be taken to minimize PCB Surface Leakage. See below section on "PCB Surface Leakage" for more details.

PCB SURFACE LEAKAGE

In applications where low input bias current is critical, Printed Circuit Board (PCB) surface leakage effects need to be considered. Surface leakage is caused by humidity, dust or other contamination on the board. Under low humidity conditions, a typical resistance between nearby traces is $10^{12}\Omega$. A 5V difference would cause 5pA of current to flow, which is greater than the LTC854x's input bias current at +25 $^{\circ}\mathrm{C}$ (\pm 1fA, typical). It is recommended to use multi-layer PCB layout and route the op-amp's –IN and +IN signal under the PCB surface.

The effective way to reduce surface leakage is to use a guard ring around sensitive pins (or traces). The guard ring is biased at the same voltage as the sensitive pin. An example of this type of layout is shown in Figure 1 for Inverting Gain application.

- 1. For Non-Inverting Gain and Unity-Gain Buffer:
 - a) Connect the non-inverting pin (+IN) to the input with a wire that does not touch the PCB surface.
 - b) Connect the guard ring to the inverting input pin (-IN). This biases the guard ring to the Common Mode input voltage.
- 2. For Inverting Gain and Trans-impedance Gain Amplifiers (convert current to voltage, such as photo detectors):
 - a) Connect the guard ring to the non-inverting input pin (+IN). This biases the guard ring to the same reference voltage as the op-amp (e.g., $V_{\rm S}/2$ or ground).
 - b) Connect the inverting pin (-IN) to the input with a wire that does not touch the PCB surface.

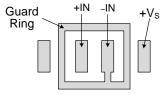


Figure 1. Use a guard ring around sensitive pins

GROUND SENSING AND RAIL TO RAIL

The input common-mode voltage range of the LTC854x series extends 100mV beyond the supply rails. This is achieved with a complementary input stage—an N-channel input differential pair in parallel with a P-channel differential pair. For normal operation, inputs should be limited to this range. The absolute maximum input voltage is 300mV beyond the supplies. Inputs greater than the input common-mode range but less than the maximum input voltage, while not valid, will not cause any damage to the op-amp. Unlike some other op-amps, if input current is limited, the inputs may go beyond the supplies without phase inversion, as shown in Figure 2. Since the input common-mode range extends from ($\rm V_{S-}-0.1V)$ to ($\rm V_{S+}+0.1V)$), the LTC854x op-amps can easily perform 'true ground' sensing.

A topology of class AB output stage with common-source transistors is used to achieve rail-to-rail output. For light

resistive loads (e.g. $50k\Omega$), the output voltage can typically swing to within 3mV from the supply rails regardless of the power-supply voltage applied. Different load conditions change the ability of the amplifier to swing close to the rails. For resistive loads up to $2\text{-}k\Omega$, the output swings typically to within 65-mV of the positive supply rail and within 45-mV of the negative supply rail.

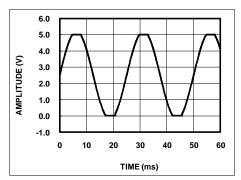


Figure 2. No Phase Inversion with Inputs Greater Than the Power-Supply Voltage

The maximum output current is a function of total supply voltage. As the supply voltage to the amplifier increases, the output current capability also increases. Attention must be paid to keep the junction temperature of the IC below 150° C when the output is in continuous short-circuit. The output of the amplifier has reverse-biased ESD diodes connected to each supply. The output should not be forced more than 0.3V beyond either supply, otherwise current will flow through these diodes.

CAPACITIVE LOAD AND STABILITY

The LTC854x can directly drive 500pF in unity-gain without oscillation. The unity-gain follower (buffer) is the most sensitive configuration to capacitive loading. Direct capacitive loading reduces the phase margin of amplifiers and this results in ringing or even oscillation. Applications that require greater capacitive drive capability should use an isolation resistor between the output and the capacitive load like the circuit in Figure 3. The isolation resistor $R_{\rm ISO}$ and the load capacitor $C_{\rm L}$ form a zero to increase stability. The bigger the $R_{\rm ISO}$ resistor value, the more stable $V_{\rm OUT}$ will be. Note that this method results in a loss of gain accuracy because $R_{\rm ISO}$ forms a voltage divider with the $R_{\rm L}$.

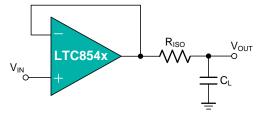


Figure 3. Indirectly Driving Heavy Capacitive Load

An improvement circuit is shown in Figure 4. It provides DC accuracy as well as AC stability. The $\rm R_F$ provides the DC accuracy by connecting the inverting signal with the output. The $\rm C_F$ and $\rm R_{\rm ISO}$ serve to counteract the loss of phase margin by feeding the high frequency component of the output signal back to the amplifier's inverting input, thereby preserving phase margin in the overall feedback loop.

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Application Notes (continued)

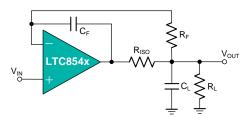


Figure 4. Indirectly Driving Heavy Capacitive Load with DC Accuracy

For no-buffer configuration, there are two others ways to increase the phase margin: (a) by increasing the amplifier's gain, or (b) by placing a capacitor in parallel with the feedback resistor to counteract the parasitic capacitance associated with inverting node.

POWER SUPPLY LAYOUT AND BYPASS

The LTC854x family operates from either a single +2.0V to +5.5V supply or dual $\pm 1.0V$ to $\pm 2.75V$ supplies. For single-supply operation, bypass the power supply V_S with a ceramic capacitor (i.e. $0.01\mu F$ to $0.1\mu F$) which should be placed close (within 2mm for good high frequency performance) to the V_S pin. For dual-supply operation, both the V_{S+} and the V_{S-} supplies should be bypassed to ground

with separate $0.1\mu F$ ceramic capacitors. A bulk capacitor (i.e. $2.2\mu F$ or larger tantalum capacitor) within 100mm to provide large, slow currents and better performance. This bulk capacitor can be shared with other analog parts.

Good PC board layout techniques optimize performance by decreasing the amount of stray capacitance at the op-amp's inputs and output. To decrease stray capacitance, minimize trace lengths and widths by placing external components as close to the device as possible. Use surface-mount components whenever possible. For the op-amp, soldering the part to the board directly is strongly recommended. Try to keep the high frequency big current loop area small to minimize the EMI (electromagnetic interfacing).

GROUNDING

A ground plane layer is important for the LTC854x circuit design. The length of the current path speed currents in an inductive ground return will create an unwanted voltage noise. Broad ground plane areas will reduce the parasitic inductance.

INPUT-TO-OUTPUT COUPLING

To minimize capacitive coupling, the input and output signal traces should not be parallel. This helps reduce unwanted positive feedback.





1.3MHz, 70µA, CMOS RRIO Operational Amplifiers

Typical Application Circuits

DIFFERENTIAL AMPLIFIER

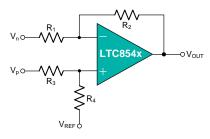


Figure 5. Differential Amplifier

The circuit shown in Figure 5 performs the difference function. If the resistors ratios are equal $R_4/R_3 = R_2/R_1$, then:

 $V_{OUT} = (V_p - V_n) \times R_2/R_1 + V_{REF}$

INSTRUMENTATION AMPLIFIER

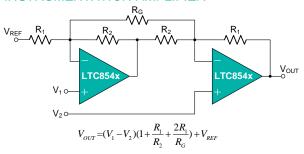


Figure 6. Instrumentation Amplifier

The LTC854x family is well suited for conditioning sensor signals in battery-powered applications. Figure 6 shows a two op-amp instrumentation amplifier, using the LTC854x op-amps. The circuit works well for applications requiring rejection of common-mode noise at higher gains. The reference voltage ($\rm V_{REF}$) is supplied by a low-impedance source. In single voltage supply applications, the $\rm V_{REF}$ is typically $\rm V_S/2$.

BUFFERED CHEMICAL SENSORS

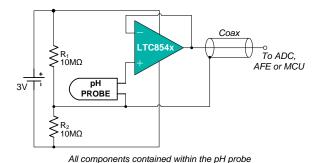


Figure 7. Buffered pH Probe

The LTC854x family has input bias current in the pA range. This is ideal in buffering high impedance chemical sensors, such as pH probes. As an example, the circuit in Figure 7 eliminates expansive low-leakage cables that that is required to connect a pH probe (general purpose combination pH probes, e.g Corning 476540) to metering ICs such as ADC, AFE and/or MCU. A LTC854x op-amp and a lithium battery are housed in the probe assembly. A conventional low-cost coaxial cable can be used to carry the op-amp's output signal to subsequent ICs for pH reading.

SHUNT-BASED CURRENT SENSING AMPLIFIER

The current sensing amplification shown in Figure 8 has a slew rate of $2\pi fV_{PP}$ for the output of sine wave signal, and has a slew rate of $2fV_{PP}$ for the output of triangular wave signal. In most of motor control systems, the PWM frequency is at 10kHz to 20kHz, and one cycle time is 100µs for a 10kHz of PWM frequency. In current shunt monitoring for a motor phase, the phase current is converted to a phase voltage signal for ADC sampling. This sampling voltage signal must be settled before entering the ADC. As the Figure 8 shown, the total settling time of a current shunt monitor circuit includes: the rising edge delay time (t_{SR}) due to the op-amp's slew rate, and the measurement settling time (t_{SET}). For a 3-shunt solution in motor phase current sensing, if the smaller duty cycle of the PWM is defined at 45% (In fact, the phase with minimum PWM duty cycle, such as 5%, is not detected current directly, and it can be calculated from the other two phase currents), and the t_{SR} is required at 20% of a total time window for a phase current monitoring, in case of a 3.3V motor control system (3.3V MCU with 12-bit ADC), the opamp's slew rate should be more than:

$3.3V/(100\mu s \times 45\% \times 20\%) = 0.37 V/\mu s$

At the same time, the op-amp's bandwidth should be much greater than the PWM frequency, like 10 time at least.

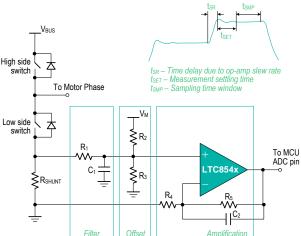


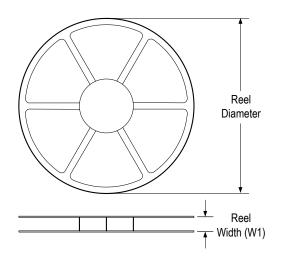
Figure 8. Current Shunt Monitor Circuit



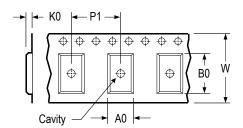


Tape and Reel Information

REEL DIMENSIONS

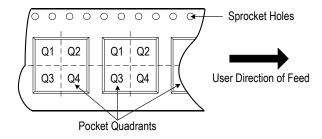


TAPE DIMENSIONS



A0	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIETATION IN TAPE



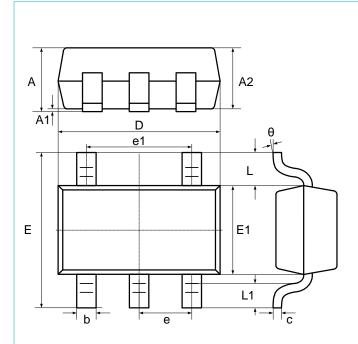
* All dimensions are nominal

	Device	Package Type	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin 1 Quadrant
LTC8	541XT5/R6	SOT23	5	3 000	178	9.0	3.3	3.2	1.5	4.0	8.0	Q3

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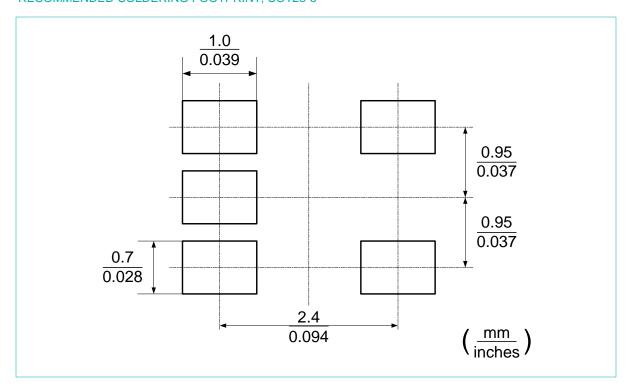
Package Outlines

DIMENSIONS, SOT23-5



	Dimer	nsions	Dimer	nsions	
Symbol	In Milli	meters	In Inches		
	Min	Max	Min	Max	
Α	-	1.25	-	0.049	
A1	0.04	0.10	0.002	0.004	
A2	1.00	1.20	0.039	0.047	
b	0.33	0.41	0.013	0.016	
С	0.15	0.19	0.006	0.007	
D	2.820	3.02	0.111	0.119	
E1	1.50	1.70	0.059	0.067	
E	2.60	3.00	0.102	0.118	
е	0.95	BSC	0.037	BSC	
e1	1.90	BSC	0.075 BSC		
L	0.60	REF	0.024 REF		
L1	0.30	0.60	0.012 0.024		
θ	0°	8°	0°	8°	

RECOMMENDED SOLDERING FOOTPRINT, SOT23-5

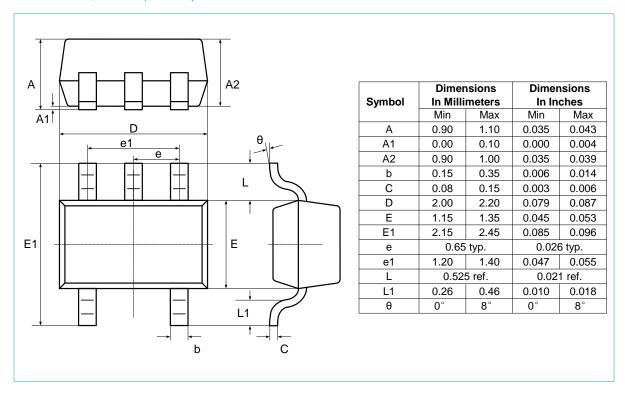




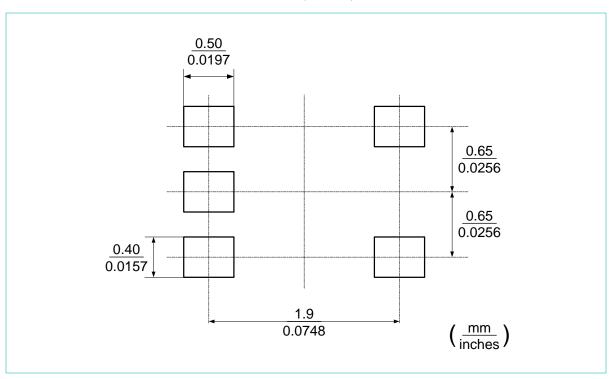


Package Outlines (continued)

DIMENSIONS, SC70-5 (SOT353)



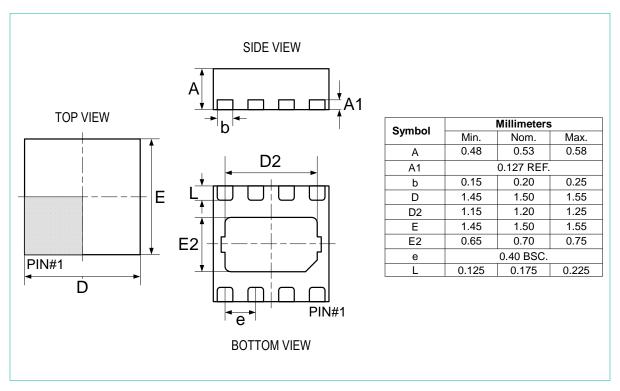
RECOMMENDED SOLDERING FOOTPRINT, SC70-5 (SOT353)



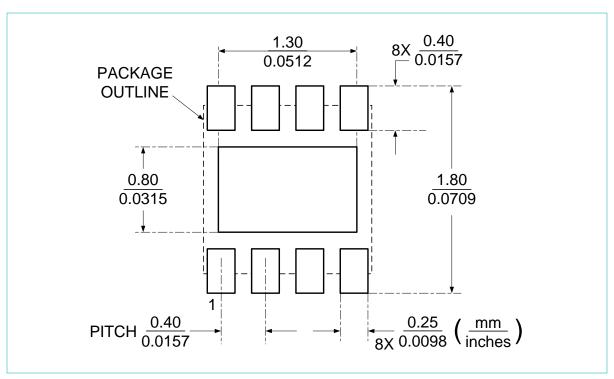
1.3MHz, 70µA, CMOS RRIO Operational Amplifiers

Package Outlines (continued)

DIMENSIONS, DFN1.5x1.5-8L



RECOMMENDED SOLDERING FOOTPRINT, DFN1.5x1.5-8L

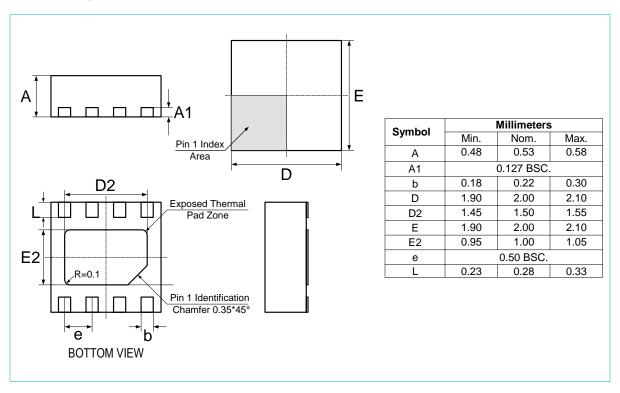




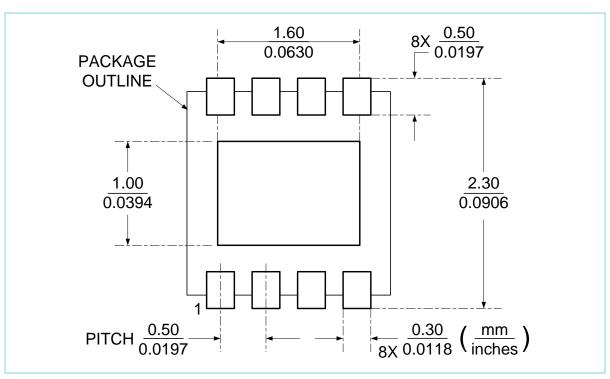


Package Outlines (continued)

DIMENSIONS, DFN2x2-8L



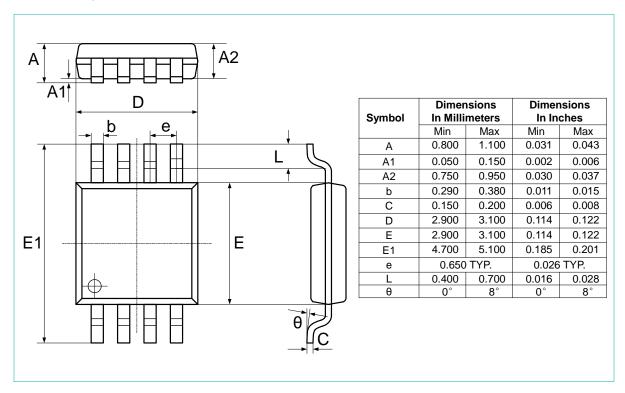
RECOMMENDED SOLDERING FOOTPRINT, DFN2x2-8L



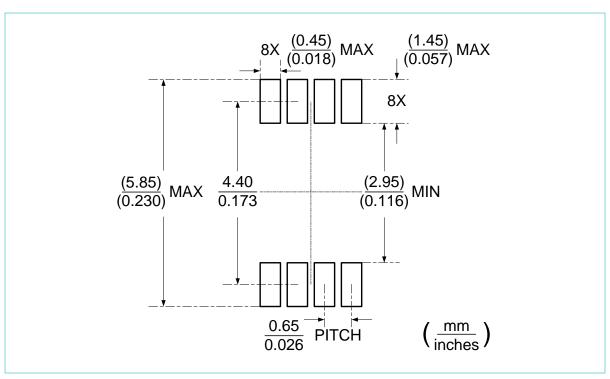
1.3MHz, 70µA, CMOS RRIO Operational Amplifiers

Package Outlines (continued)

DIMENSIONS, MSOP-8L



RECOMMENDED SOLDERING FOOTPRINT, MSOP-8L

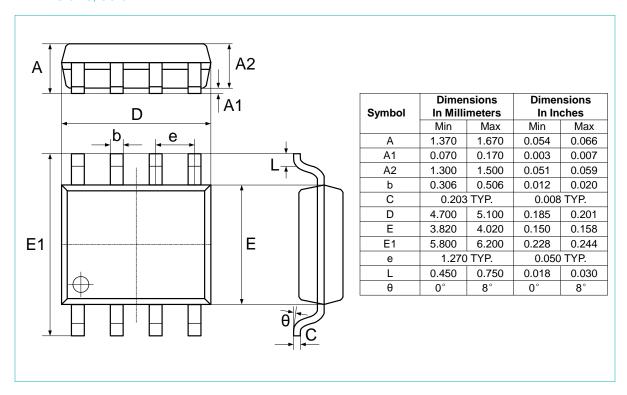




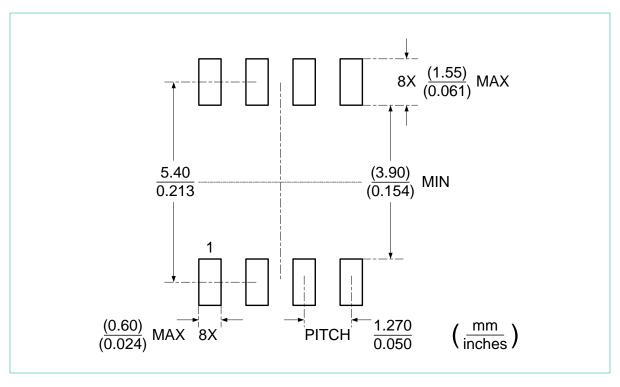


Package Outlines (continued)

DIMENSIONS, SO-8



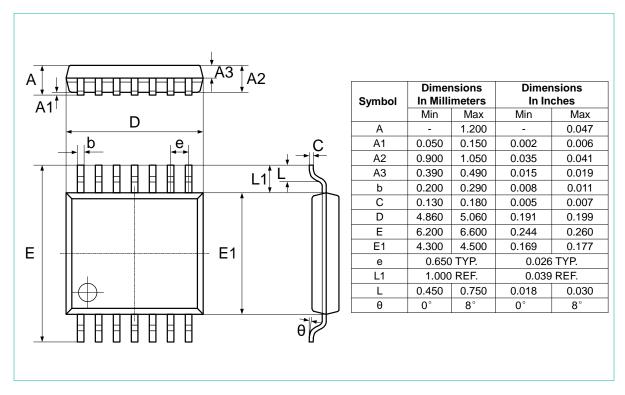
RECOMMENDED SOLDERING FOOTPRINT, SO-8



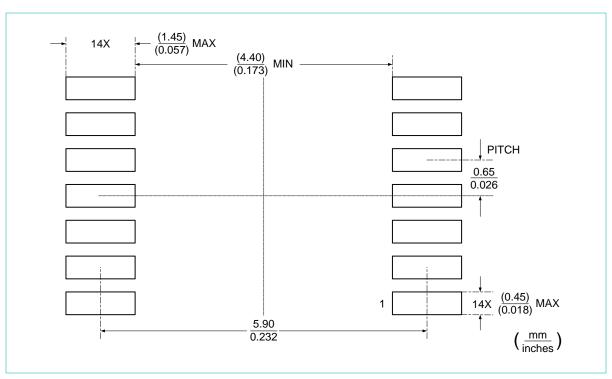
1.3MHz, 70µA, CMOS RRIO Operational Amplifiers

Package Outlines (continued)

DIMENSIONS, TSSOP-14L



RECOMMENDED SOLDERING FOOTPRINT, TSSOP-14L

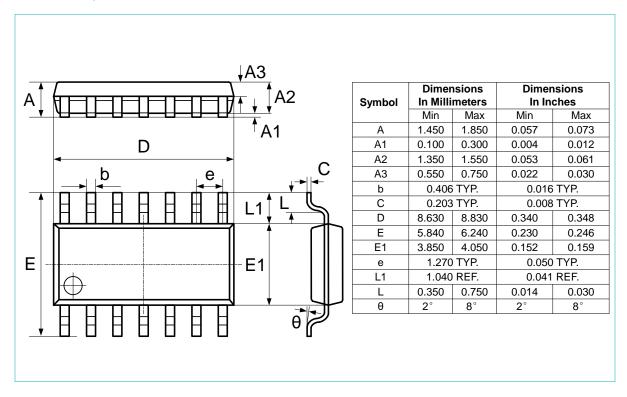




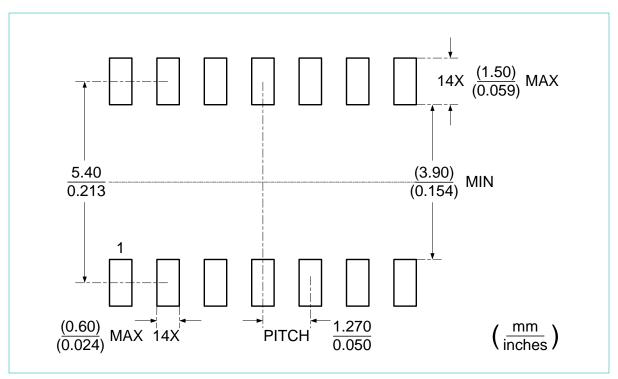


Package Outlines (continued)

DIMENSIONS, SO-14



RECOMMENDED SOLDERING FOOTPRINT, SO-14





1.3MHz, 70µA, CMOS RRIO Operational Amplifiers

IMPORTANT NOTICE

Linearin is a global fabless semiconductor company specializing in advanced high-performance high-quality analog/mixed-signal IC products and sensor solutions. The company is devoted to the innovation of high performance, analog-intensive sensor front-end products and modular sensor solutions, applied in multi-market of medical & wearable devices, smart home, sensing of IoT, and intelligent industrial & smart factory (industrie 4.0). Linearin's product families include widely-used standard catalog products, solution-based application specific standard products (ASSPs) and sensor modules that help customers achieve faster time-to-market products. Go to http://www.linearin.com for a complete list of Linearin product families.

For additional product information, or full datasheet, please contact with the Linearin's Sales Department or Representatives.